	L #	Hits	Search Text	DBs	Time Stamp
1	L1	246110	substrate with insulat$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 14:42
2	L2	104920	1 same (semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 14:46
3	L3	78446	2 and @pd<20010626	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 14:47
4	L4	32753	3 and etch$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 14:47
5	L5	44	4 and 216/41.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 14:51
6	L6	21	5 and (silicon same (silicon near2 oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 14:57
7	L7	9	6 and (nano or "nm")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 15:01
8	L8	9	7 and (aluminum or "Al")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 15:41

	L #	Hits	Search T xt	DBs	Time Stamp
9	L9	103	((metal near silicide) near5 mask$3) same (silicon same etch$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 15:42
10	L10	2	9 same ((nano near structure) or (nano near wire) or "nm")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 15:45